GSM4701S

40V N+P Dual Channel MOSFETs

Product Description

These N+P dual Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode.

These devices are well suited for high efficiency fast switching applications.

Features

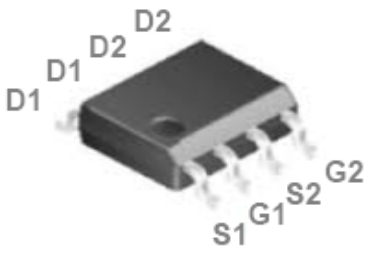
- N-Channel
  40V, 6.7A, $R_{DS(ON)}$=32mΩ@V_{GS}=10V
- P-Channel
  -40V, -7.2A, $R_{DS(ON)}$=40mΩ@V_{GS}=-10V
- Fast switching
- Suit for 4.5V / -4.5V Gate Drive Applications
- Green Device Available

Applications

- DC Fan
- Motor Drive Applications
- Networking
- Half / Full Bridge Topology

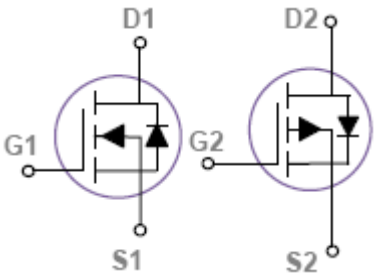
Packages & Pin Assignments

GSM4701SF (SOP-8)

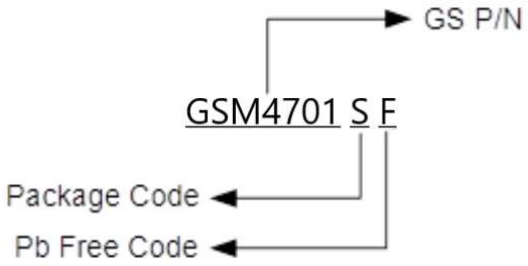


Top View

Pin	Description
1	Source 1
2	Gate 1
3	Source 2
4	Gate 2
5	Drain 2
6	Drain 2
7	Drain 1
8	Drain 1

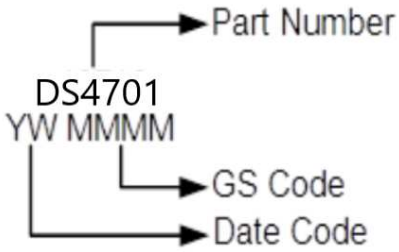


Ordering Information



Part Number	Package	Quantity Reel
GSM4701SF	SOP-8	4000 PCS

Marking Information



Absolute Maximum Ratings

T_C=25ºC Unless otherwise noted

Symbol	Parameter		*Typical*		Unit
			N-Channel	*P-Channel*	
V_{DS}	Drain-Source Voltage		40	-40	V
V_{GS}	Gate-Source Voltage		±20	±20	V
I_D	Continuous Drain Current	T_C=25℃	6.7	-7.2	A
		T_C=100℃	4.3	-4.5	
I_{DM}	Pulsed Drain Current[1]		26.8	-28.8	A
P_D	Power Dissipation	T_C=25℃	2.5		W
		Derate above 25℃	0.02		W/℃
T_J	Operating Junction Temperature Range		-55 to +150		℃
T_{STG}	Storage Temperature Range		-55 to +150		℃
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient		62		℃/W
$R_{\theta JC}$	Thermal Resistance-Junction to Case		50		℃/W

Electrical Characteristics (N-Channel)

T_J=25℃ Unless otherwise noted

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V,I_D=250uA	40			V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS},I_D=250uA	1.0	1.8	2.5	V
△$V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient			-3		mV/℃
I_{GSS}	Gate-Source Leakage Current	V_{DS}=0V,V_{GS}=±20V			±100	nA
I_{DSS}	Drain-Source Leakage Current	V_{DS}=30V,V_{GS}=0V			1	uA
		V_{DS}=24V,V_{GS}=0V, T_J=125℃			10	
I_S	Continuous Source Current	V_G=V_D=0V, Force Current			6.7	A
I_{SM}	Pulsed Source Current				13.4	
$R_{DS(on)}$	Drain-Source On-Resistance	V_{GS}=10V,I_D=5A		24	32	mΩ
		V_{GS}=4.5V,I_D=3A		32	45	
g_{FS}	Forward Transconductance	V_{DS}=10V,I_D=3A		3.6		S
V_{SD}	Diode Forward Voltage	V_{GS}=0V,I_S=1A			1	V
Dynamic						
Q_g	Total Gate Charge[2,3]	V_{DS}=20V,V_{GS}=4.5V, I_D=3A		2.8	5.6	nC
Q_{gs}	Gate-Source Charge[2,3]			0.5	1	
Q_{gd}	Gate-Drain Charge[2,3]			1.5	3	
C_{iss}	Input Capacitance	V_{DS}=15V,V_{GS}=0V, f=1MHz		420	800	pF
C_{oss}	Output Capacitance			65	120	
C_{rss}	Reverse Transfer Capacitance			40	80	
$t_{d(on)}$	Turn-On Time[2,3]	V_{DD}=20V,I_D=1A, V_{GS}=4.5V,R_G=25Ω		3.2	6	ns
t_r				8.6	16	
$t_{d(off)}$	Turn-Off Time[2,3]			18	36	
t_f				6	12	

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%.
3. Essentially independent of operating temperature.

Electrical Characteristics (P-Channel)

T_J=25℃ Unless otherwise noted

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V,I_D=-250uA	-40			V
$\triangle BV_{DSS}/\triangle T_J$	BV_{DSS} Temperature Coefficient	Reference to 25℃, I_D=-1mA		-0.04		V/℃
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS},I_D=-250uA	-1	-1.6	-2.5	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient			3		mV/℃
I_{GSS}	Gate-Source Leakage Current	V_{DS}=0V,V_{GS}=±20V			±100	nA
I_{DSS}	Drain-Source Leakage Current	V_{DS}=-40V,V_{GS}=0V			-1	uA
		V_{DS}=-32V,V_{GS}=0V, T_J=125℃			-10	
I_S	Continuous Source Current	V_G=V_D=0V, Force Current			-7.2	A
I_{SM}	Pulsed Source Current				-14.4	
$R_{DS(on)}$	Drain-Source On-Resistance	V_{GS}=-10V,I_D=-4A		32	40	mΩ
		V_{GS}=-4.5V,I_D=-2A		45	60	
g_{FS}	Forward Transconductance	V_{DS}=-10V,I_D=-3A		5		S
V_{SD}	Diode Forward Voltage	V_{GS}=0V,I_S=-1A			-1	V
Dynamic						
Q_g	Total Gate Charge[2,3]	V_{DS}=-20V,V_{GS}=-4.5V, I_D=-2A		8	16	nC
Q_{gs}	Gate-Source Charge[2,3]			2.1	4.2	
Q_{gd}	Gate-Drain Charge[2,3]			3.6	7.2	
C_{iss}	Input Capacitance	V_{DS}=-15V,V_{GS}=0V, f=1MHz		1050	1600	pF
C_{oss}	Output Capacitance			110	160	
C_{rss}	Reverse Transfer Capacitance			80	120	
$t_{d(on)}$	Turn-On Time[2,3]	V_{DD}=-20V,I_D=-1A, V_{GS}=-4.5V,R_G=25Ω		20	40	ns
t_r				12	24	
$t_{d(off)}$	Turn-Off Time[2,3]			46	80	
t_f				6	12	

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%.
3. Essentially independent of operating temperature.

Typical Performance Characteristics (N-Channel)

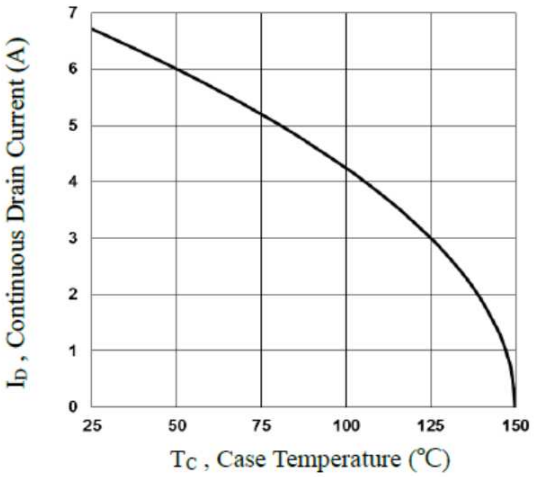


Fig.1 Continuous Drain Current vs. T_c

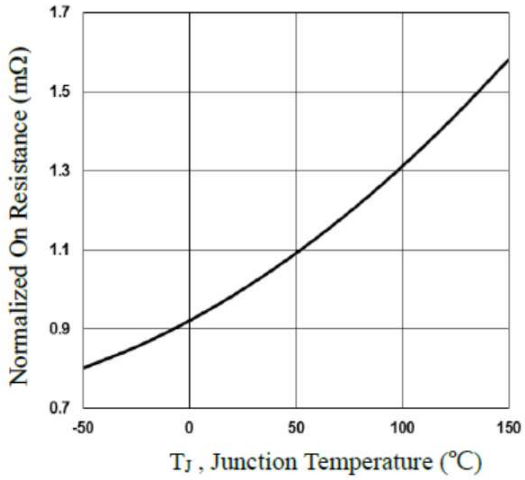


Fig.2 Normalized RDSON vs. T_J

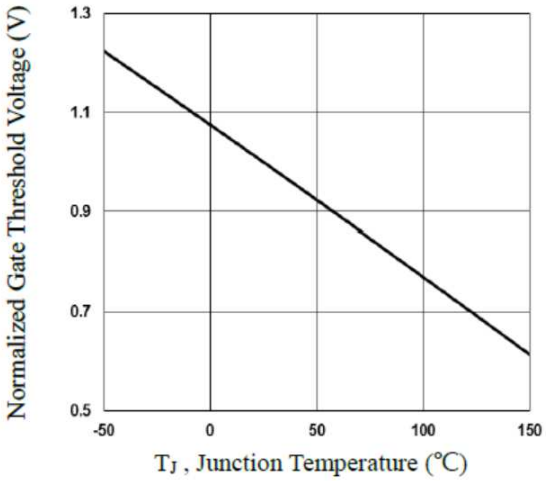


Fig.3 Normalized V_{th} vs. T_J

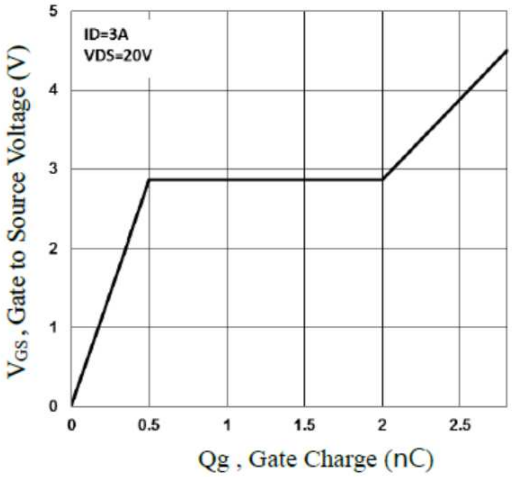


Fig.4 Gate Charge Waveform

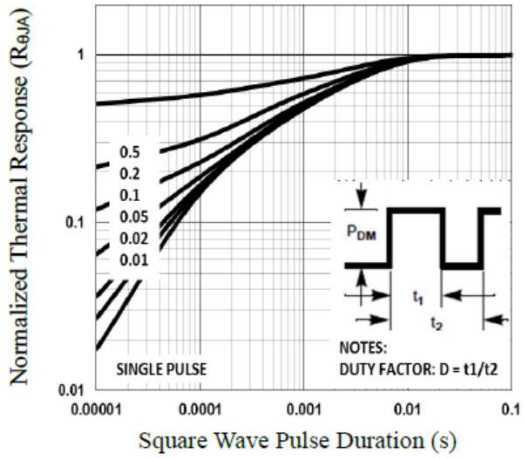


Fig.5 Normalized Transient Impedance

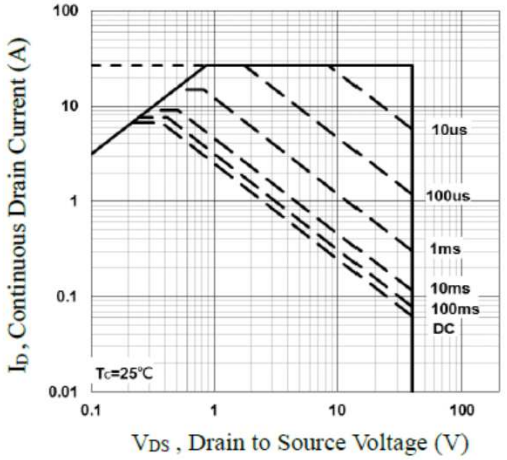


Fig.6 Maximum Safe Operation Area

Typical Performance Characteristics (P-Channel)

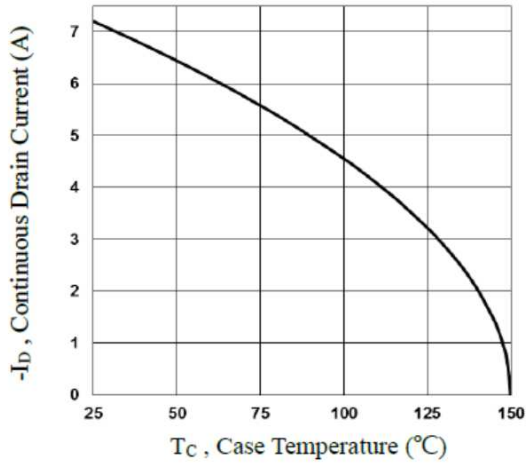


Fig.7 Continuous Drain Current vs. T_c

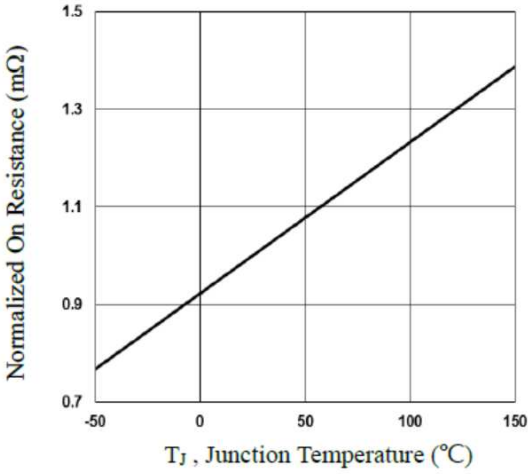


Fig.8 Normalized RDSON vs. T_J

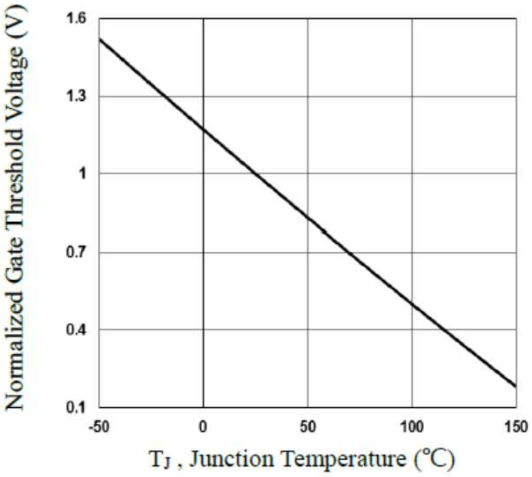


Fig.9 Normalized V_{th} vs. T_J

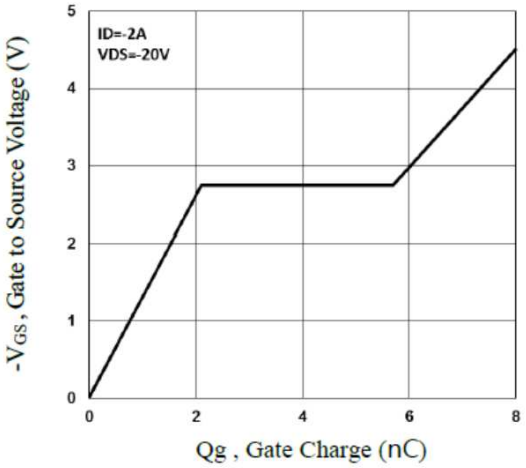


Fig.10 Gate Charge Waveform

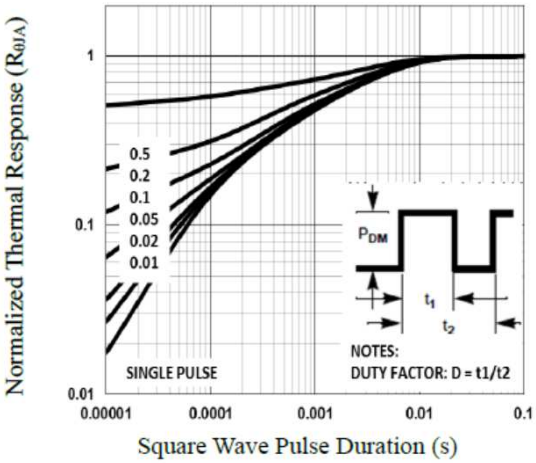


Fig.11 Normalized Transient Impedance

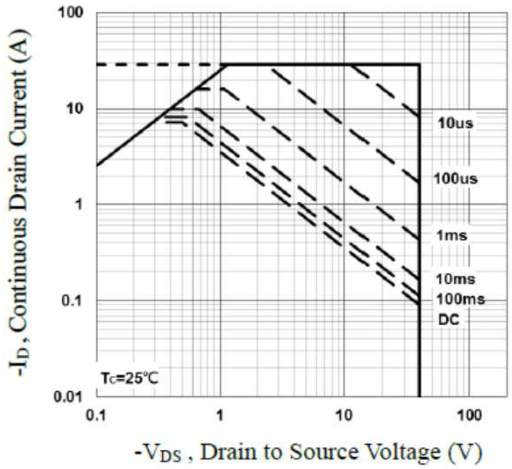
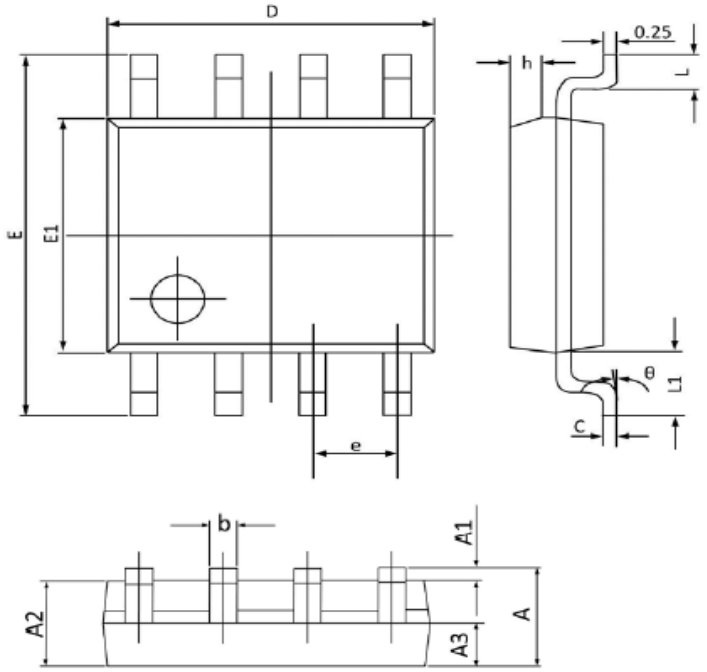


Fig.12 Maximum Safe Operation Area

Package Dimension

SOP-8



Dimensions				
Symbol	Millimeters		Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.068
A1	0.100	0.250	0.004	0.009
A2	1.300	1.500	0.052	0.059
A3	0.600	0.700	0.024	0.027
b	0.390	0.480	0.016	0.018
c	0.210	0.260	0.009	0.010
D	4.700	5.100	0.186	0.200
E	5.800	6.200	0.229	0.244
E1	3.700	4.100	0.146	0.161
e	1.270 (BSC)		0.050 (BSC)	
h	0.250	0.500	0.010	0.019
L	0.500	0.800	0.019	0.031
L1	1.050 (BSC)		0.041 (BSC)	
θ	0°	8°	0°	8°

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